

ABSTRACT

A method for forming a structure element in a layer arranged on a wafer by a trimming mask set, a developing step, and an etching step for the transfer of the structure pattern are carried out between the exposure steps carried out by the masks. Consequently, edges that are incipiently exposed below a limit value for the structure formation around the
5 resist structures in a first resist layer, which are exposed using a first mask of the set, are transferred dimensionally accurately into an underlying layer on the wafer. Then, the exposure postprocesses the pattern of the first mask using a second mask of the set, the trimming mask, into a second, subsequently applied second resist layer.